



February 11, 2004

To: Commissioner for Patents  
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Subject: | Serial No. 10/718,877 11/21/03 |

Shih-Wei Wang et al.

ENDURANCE IMPROVEMENT BY SIDEWALL  
NITRIDATION OF POLY FLOATING GATE  
FOR NONVOLATILE MEMORY DEVICES USING  
SUBSTRATE OR DRAIN-SIDE ERASE SCHEME

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56.

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner for Patents,  
P.O. Box 1450, Alexandria, VA 22313-1450, on February , 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date Stephen B. Ackerman 2/12/04

U.S. Patent 6,417,046 to Ho et al., "Modified Nitride Spacer for Solving Charge Retention Issue in Floating Gate Memory Cell," discloses a modified nitride spacer with significantly improved charge retention in floating gate memory cells.

U.S. Patent 6,184,088 to Kurooka et al., "Method for Manufacturing a Split Gate Type Transistor," teaches a method to fabricate a split-gate type transistor with a nitrated floating gate.


U.S. Patent 6,268,624 to Sobek et al., "Method for Inhibiting Tunnel Oxide Growth at the Edges of a Floating Gate during Semiconductor Device Process," discloses a method for inhibiting tunnel oxide thickening by forming protective barrier films.

U.S. Patent 5,966,606 to Ono, "Method for Manufacturing a MOSFET having a Side-wall Film Formed through Nitridation of the Gate Electrode," discloses a method for forming a sidewall film of a gate electrode by forming a thin silicon nitride film through nitridation of the gate electrode and a relatively thick silicon nitride film.

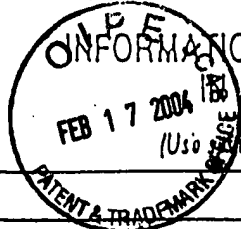
TSMC-02-622

U.S. Patent 5,827,769 to Aminzadeh et al., "Method for Fabricating a Transistor with Increased Hot Carrier Resistance by Nitridizing and Annealing the Sidewall Oxide of the Gate Electrode," discloses a method for fabricating a transistor by nitridizing the sidewall oxide of the gate electrode.

Sincerely,

  
Stephen B. Ackerman,  
Reg. No. 37761

Form PTO-1449



# INFORMATION DISCLOSURE CITATION IN AN APPLICATION

Document Number (Optional)

TSMC-02-622

Application Number

10/718,877

Applicant

Shih-Wei Wang et al.

Filing Date

11/21/03

Group Art Unit

## U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6417046	7/9/02	Ho et al.	438	257	5/5/00
	6184088	2/6/01	Kurooka et al.	438	264	2/25/99
	6268624	7/31/01	Sobek et al.	257	321	7/31/99
	5966606	10/12/99	Ono	438	303	5/14/97
	5827769	10/27/98	Aminzadeh et al.	438	305	11/20/96

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)


EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.